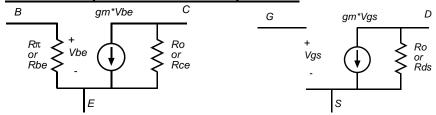
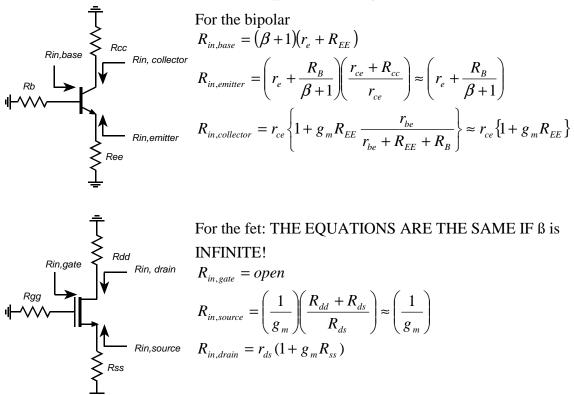
Basics: Amplifiers at Low Frequencies



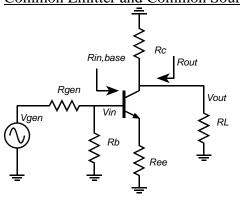
Left is the equivalent circuit of a bipolar transistor; $g_m = I_E/V_T = 1/r_e$, $V_T = kT/q$, $r_\pi = r_{be} = \beta/g_m$. $R_{ce} = (V_A + V_{CE})/I_C$. On the right is the FET model. $g_m = v_{sat}c_{ox}W_g$ (short-gate / velocity saturation model), $R_{ds} = [(1/\lambda) + V_{DS}]/I_D$



Be warned that in the equations above Rcc, REE and RB are the equivalent resistances seen by the transistor. So in, the amplifier circuits below, THINK: "what is the effective resistance seen by the transistor?", before plugging into the equations.

Amplifier Stages





Common emitter:

Rin,base

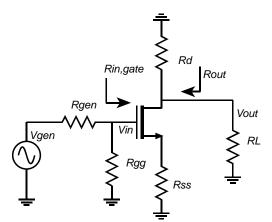
Rout

$$R_{in} = R_B \| R_{in,base} = R_B \| (\beta + 1)(R_{EE} + r_e)$$

$$V_{in} = \frac{R_{in}}{R_{in} + R_{gen}}$$

$$A_V = \frac{V_{out}}{V_{in}} = \frac{-R_{Leq}}{r_e + R_{ee}} = \frac{-(R_c \| R_L \| R_{out,collector})}{r_e + R_{ee}}$$

$$R_{out} = R_c \| R_{out,collector}$$



Common source:
$$R_{in} = R_{gg}$$

$$V_{in} = \frac{R_{in}}{R_{in} + R_{gen}}$$

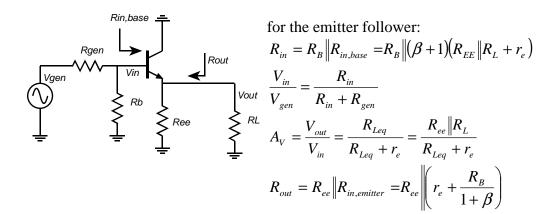
$$R_{in} = R_{gg}$$

$$V_{in} = \frac{R_{in}}{R_{in} + R_{gen}}$$

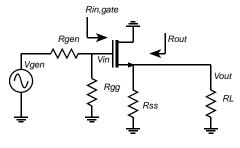
$$R_{in} = R_{gen}$$

$$R_{in} = R_{gen$$

Common Collector (emitter follower) and common drain (source follower)



Single stage amplifier crib sheet, page 3



For the source follower:

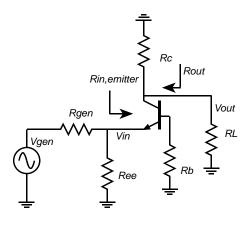
For the source follower:
$$R_{in} = R_{g}$$

$$Vout \qquad V_{in} = \frac{R_{in}}{R_{in} + R_{gen}}$$

$$A_{V} = \frac{V_{out}}{V_{in}} = \frac{R_{Leq}}{R_{Leq} + 1/g_{m}} = \frac{R_{ss} \|R_{L}}{R_{Leq} + 1/g_{m}}$$

$$R_{out} = R_{ss} \|R_{in.source} = R_{ss}\| (1/g_{m})$$

Common Base and common gate



For the common base:

For the common base:
$$R_{in} = R_{EE} \| R_{in,emitter}$$

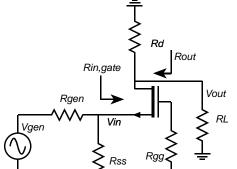
$$R_{in,emitter} = \left(r_e + \frac{R_B}{\beta + 1} \right) \left(\frac{r_{ce} + R_c \| R_L}{r_{ce}} \right) \approx \left(r_e + \frac{R_B}{\beta + 1} \right)$$

$$R_{in,emitter} = \left(r_e + \frac{R_B}{\beta + 1} \right) \left(\frac{r_{ce} + R_c \| R_L}{r_{ce}} \right) \approx \left(r_e + \frac{R_B}{\beta + 1} \right)$$

$$R_{in,emitter} = \frac{R_{in}}{R_{in} + R_{gen}}$$

$$R_{in} = \frac{R_{leq}}{R_{in,emitter}} = \frac{R_C \| R_L}{R_{in,emitter}}$$

$$R_{out} = R_c \| R_{out,collector}$$



For the common gate

Rin, gate

Rin, gate

Rout

$$R_{in} = R_{SS} \| R_{in, source}$$

$$R_{in, emitter} = \left(\frac{1}{g_m}\right) \left(\frac{r_{ds} + R_d \| R_L}{r_{ds}}\right) \approx \left(\frac{1}{g_m}\right)$$

Resorred

$$R_{in} = R_{SS} \| R_{in, source}$$

$$R_{in, emitter} = \left(\frac{1}{g_m}\right) \left(\frac{r_{ds} + R_d \| R_L}{r_{ds}}\right) \approx \left(\frac{1}{g_m}\right)$$

$$R_{in, emitter} = \frac{R_{in}}{R_{in} + R_{gen}}$$

$$R_{in, source} = \frac{R_{in}}{R_{in, source}}$$

$$R_{in, source} = \frac{R_{in}}{R_{in, source}}$$